

3SK272

GaAs N-Channel MES FET

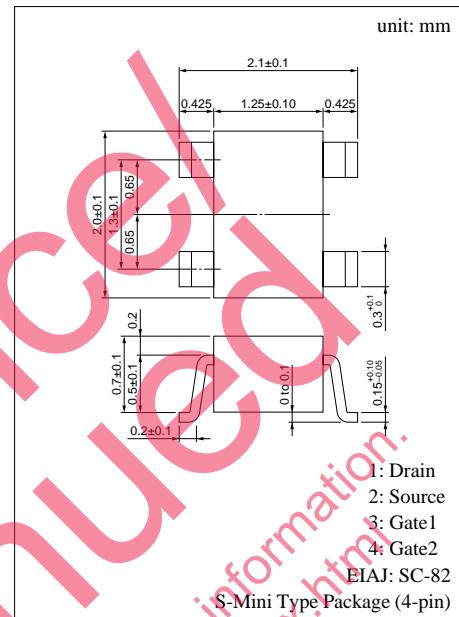
For VHF-UHF amplification

■ Features

- Low noise-figure (NF)
- Large power gain PG
- S-mini type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

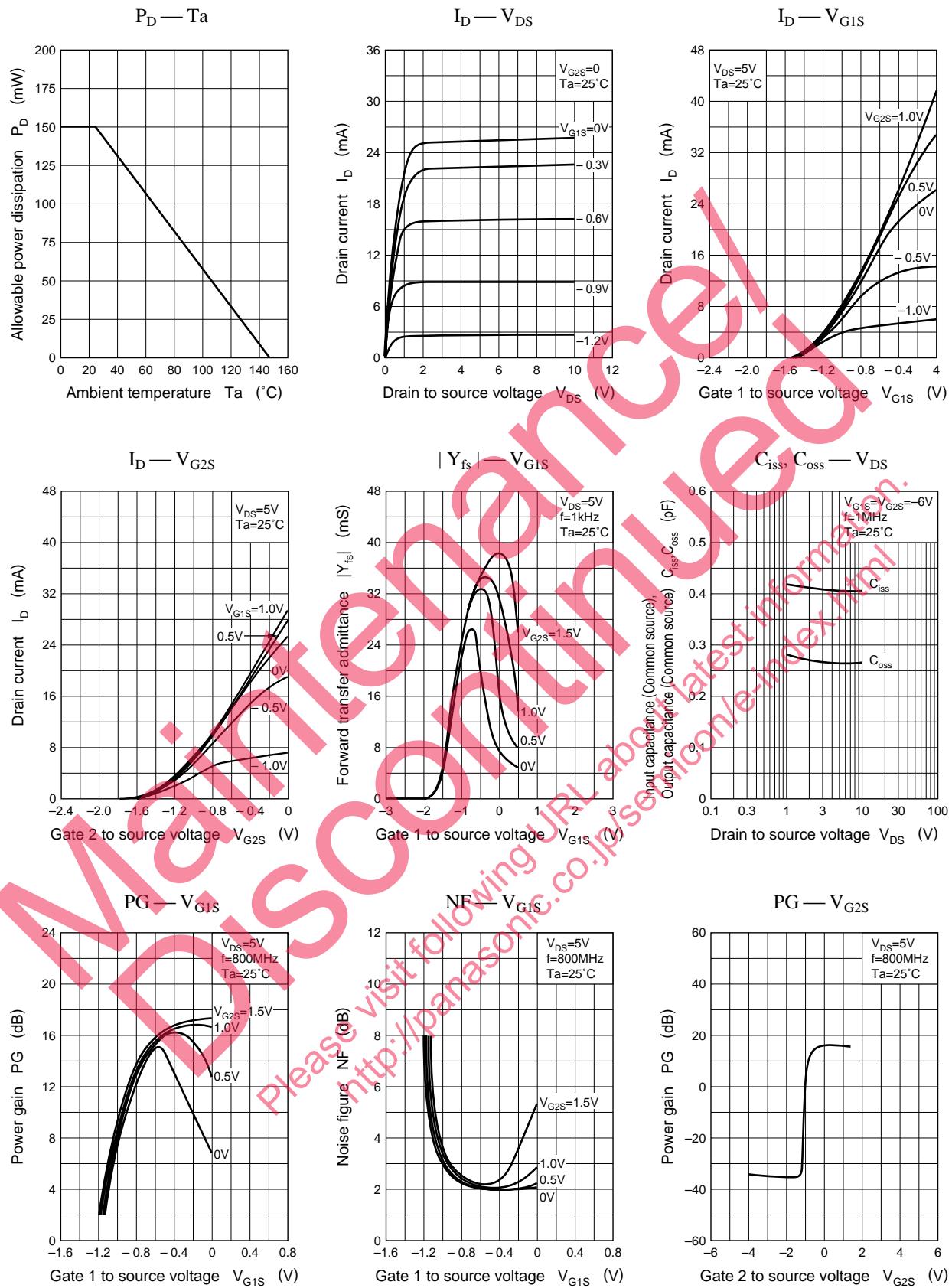
Parameter	Symbol	Ratings	Unit
Drain to Source voltage	V_{DS}	13	V
Gate 1 to Source voltage	V_{G1S}	-6	V
Gate 2 to Source voltage	V_{G2S}	-6	V
Drain current	I_D	50	mA
Gate 1 current	I_{G1}	1	mA
Gate 2 current	I_{G2}	1	mA
Allowable power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

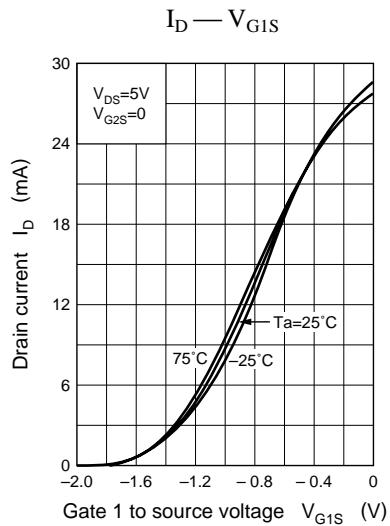


Marking Symbol: DU

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSs}	$V_{DS} = 5\text{V}$, $V_{G1S} = 0$, $V_{G2S} = 0$	8.5		35	mA
Gate 2 to Drain current	I_{G2DO}	$V_{G2D} = -13\text{V}$ ($G1, S = \text{Open}$)			50	μA
Gate 1 cut-off current	I_{G1SS}	$V_{DS} = V_{G2S} = 0$, $V_{G1S} = -6\text{V}$			-20	μA
Gate 2 cut-off current	I_{G2SS}	$V_{DS} = V_{G1S} = 0$, $V_{G2S} = -6\text{V}$			-20	μA
Drain cut-off current	I_{DSX}	$V_{DS} = 13\text{V}$, $V_{G1S} = -3.5\text{V}$, $V_{G2S} = 0$			50	μA
Gate 1 to Source cut-off voltage	V_{G1SC}	$V_{DS} = 5\text{V}$, $V_{G2S} = 0$, $I_D = 200\mu\text{A}$			-3.5	V
Gate 2 to Source cut-off voltage	V_{G2SC}	$V_{DS} = 5\text{V}$, $V_{G1S} = 0$, $I_D = 200\mu\text{A}$			-3.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 5\text{V}$, $I_D = 10\text{mA}$, $V_{G2S} = 1.5\text{V}$, $f = 1\text{kHz}$	18	23		mS
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 5\text{V}$, $V_{G1S} = V_{G2S} = -6\text{V}$ $f = 1\text{MHz}$		0.4	2	pF
Output capacitance (Common Source)	C_{oss}			0.3	1.2	pF
Reverse transfer capacitance (Common Source)	C_{rss}			0.02	0.04	pF
Power gain	PG	$V_{DS} = 5\text{V}$, $I_D = 10\text{mA}$	10	16		dB
Noise figure	NF	$V_{G2S} = 1.5\text{V}$, $f = 800\text{MHz}$		1.8	2.8	dB
Gain reduction	G_R	$V_{DS} = 5\text{V}$, $V_{AGC} = 1.5\text{V}/-3.5\text{V}$, $f = 800\text{MHz}$	37	45		dB





Maintenance Discontinued!

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